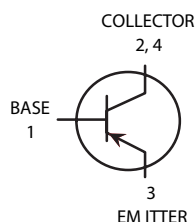


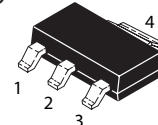
PNP Silicon Planar High Current Transistor

(Pb) Lead(Pb)-Free



SOT-223

1.BASE
2.COLLECTOR
3.EMITTER
4.COLLECTOR



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Collector to Base Voltage	V_{CB0}	-100	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Collector to Base Voltage	V_{EBO}	-6	V
Collector Current	$I_C(\text{DC})$	-5	A
Collector Current	$I_C(\text{Pulse})$	-15	A
Total Device Dissipation $T_A=25^\circ\text{C}$	P_D	3	W
Junction Temperature	T_j	+150	$^\circ\text{C}$
Storage, Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

*Device mounted in a typical manner on a P.C.B with copper 4 inches x 4 inches(min).

Device Marking

PZT951=PZT951

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Max	Unit
Collector-Base Breakdown Voltage $I_C=-100\mu\text{A}, I_E=0$	BV_{CB0}	-100	-	-	V
Collector-Emitter Breakdown Voltage $I_C=-1\mu\text{A}, R_B\leq 1\text{k}\Omega$	BV_{CER}	-100	-	-	V
Collector-Emitter Breakdown Voltage ⁽¹⁾ $I_C=-10\text{mA}, I_B=0$	BV_{CEO}	-60	-	-	V
Emitter-Base Breakdown Voltage $I_E=-100\mu\text{A}, I_C=0$	BV_{EBO}	-6	-	-	V
Collector Cut-Off Current $V_{CB}=-80\text{V}, I_E=0$	I_{CBO}	-	-	-50	nA
Collector Cut-Off Current $V_{CB}=-80\text{V}, R\leq 1\text{k}\Omega$	I_{CER}	-	-	-50	nA
Emitter-Cut-Off Current $V_{EB}=-6\text{V}, I_C=0$	I_{EBO}	-	-	-10	nA

ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

ON CHARACTERISTICS⁽¹⁾

DC Current Gain V _{CE} =-1V, I _C =-10mA	h _{FE1}	100	200	-	
V _{CE} =-1V, I _C =-2A	h _{FE2}	100	200	300	-
V _{CE} =-1V, I _C =-5A	h _{FE3}	75	90	-	
V _{CE} =-1V, I _C =-10A	h _{FE4}	10	25	-	
Collector-Emitter Saturation Voltage I _C =-100mA, I _B =-10mA	V _{CE(sat)}	-	-20	-50	mV
I _C =-1A, I _B =-100mA		-	-85	-140	
I _C =-2A, I _B =-200mA		-	-155	-210	
I _C =-5A, I _B =-500mA		-	-370	-460	
Base-Emitter Saturation Voltage I _C =-5A, I _B =-500mA	V _{BE(sat)}	-	-1.08	-1.24	V
Base-Emitter On Voltage V _{CE} =-1V, I _C =-5A	V _{BE(on)}	-	-0.935	-1.07	V

DYNAMIC CHARACTERISTICS

Transition Frequency V _{CE} =-10V, I _C =-100mA, f=50MHz	f _T	-	120	-	MHz
Output Capacitance V _{CB} =-10V, I _E =0, f=1MHz	C _{ob}	-	74	-	pF

SWITCHING TIMES

Switching Times I _C =-2A, I _{B1} =-200mA V _{CC} =-10V, I _{B2} =-200mA	t _{on}	-	82	-	ns
	t _{off}	-	350	-	

Note 1.Pulse Test : Pulse width < 300μs, Duty cycle ≤ 20%.

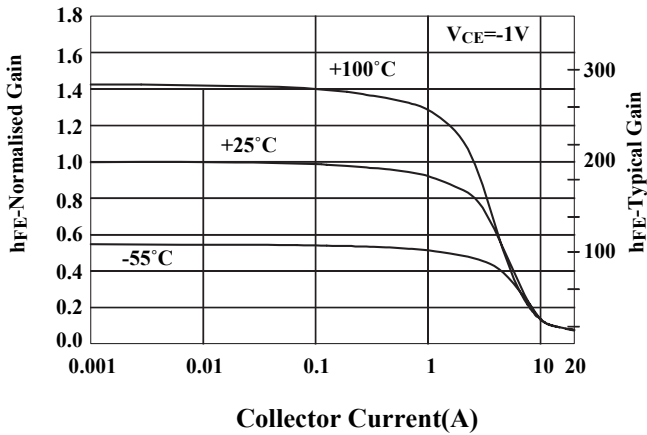


Fig.1 Current Gain & Collector Current

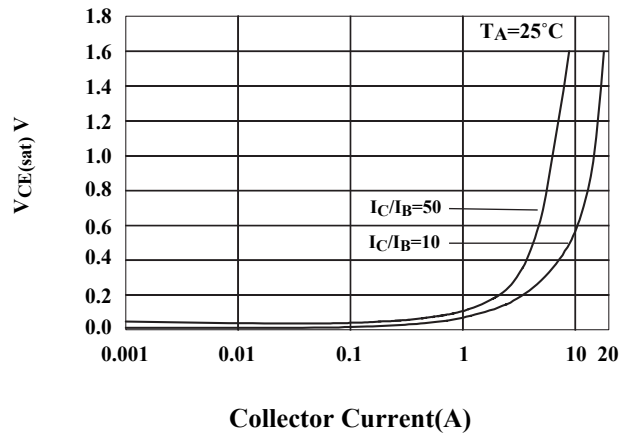


Fig.2 Saturation Voltage & Collector Current

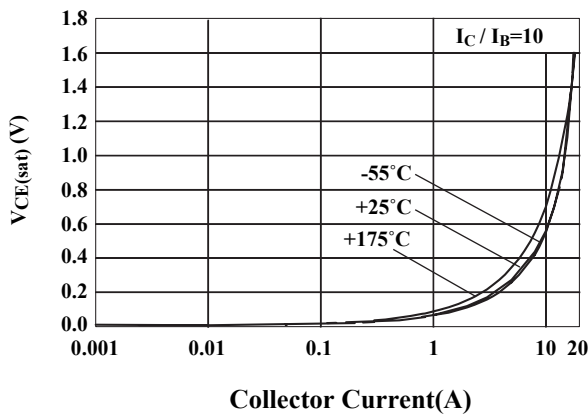


Fig.3 Saturation Voltage & Collector Current

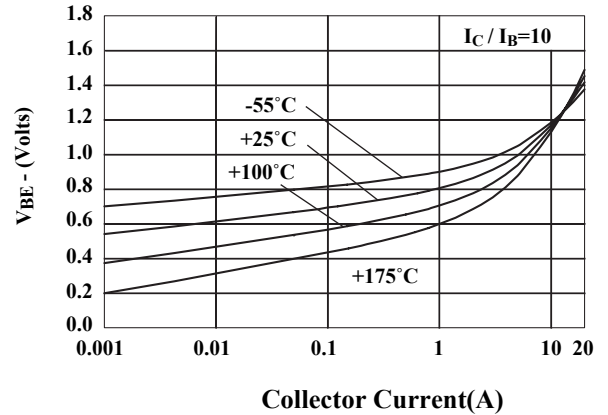


Fig.4 Saturation Voltage & Collector Current

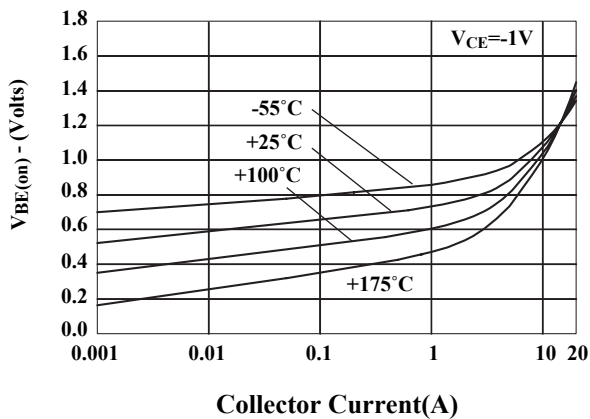


Fig.5 On Voltage & Collector Current

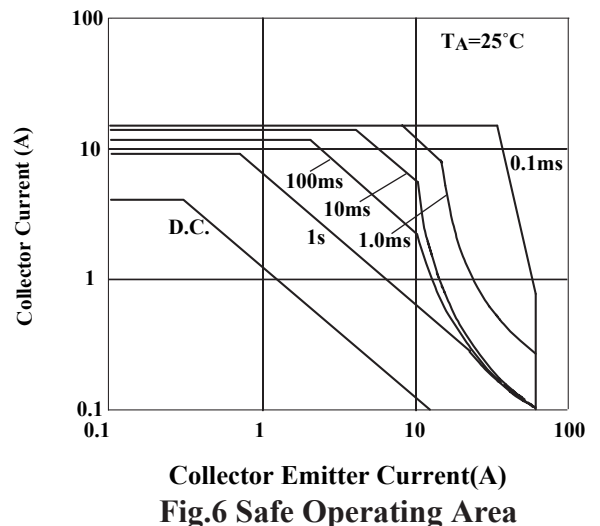
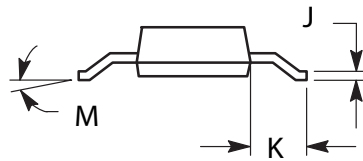
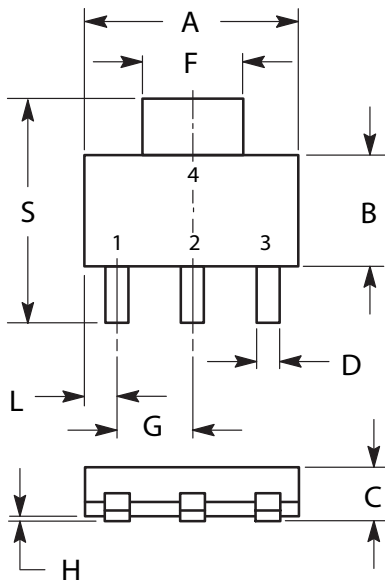


Fig.6 Safe Operating Area

SOT-223 Outline Dimensions

unit:mm



DIM	MILLIMETERS	
	MIN	MAX
A	6.30	6.70
B	3.30	3.70
C	1.50	1.75
D	0.60	0.89
F	2.90	3.20
G	2.20	2.40
H	0.020	0.100
J	0.24	0.35
K	1.50	2.00
L	0.85	1.05
M	0°	10°
S	6.70	7.30